Abstract for Invited Talk (invited by Dr. Dan Botez)

Optoelectronics '97
In-Plane Semiconductor Lasers: from Ultraviolet to Mid-Infrared
Conference Chair: Dr. Peter Zory

Abstract Title: "High-Power Laser Diodes at 808, 941 and 1800 nm"

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PRESENTATION: Oral Presentation

ABSTRACT:

The design and implementation of a laser diode structure having a large transverse mode size are described. Performance and reliability data are presented on high-power operation, at 808 and 941 nm, of 1 cm diode bars utilizing this design, and comparisons are made to diode structures having a smaller transverse mode size. In addition, 1.8 μm high-power diode arrays fabricated in both the InGaAsP/InP and InAlGaAs/InP material systems are described.

KEY WORDS:

laser diodes

BIOGRAPHY OF PRINCIPAL AUTHOR:

Mark A. Emanuel is an engineer at Lawrence Livermore National Laboratory. His research interests include the design of optoelectronic devices and their growth by MOCVD.

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